

# RJK4013DPE

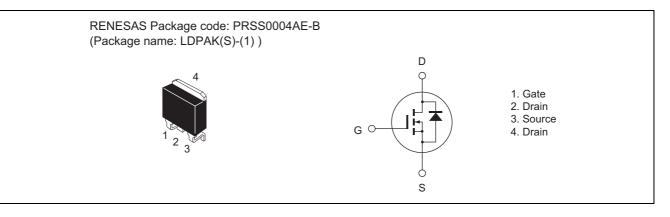
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1513-0100 Rev.1.00 Feb 02, 2007

# Features

- Low on-resistance
- Low leakage current
- High speed switching

# Outline



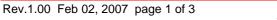
# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ Item Symbol Ratings Unit Drain to source voltage V<sub>DSS</sub> 400 V V Gate to source voltage V<sub>GSS</sub> ±30 17 A Drain current  $I_D$ Note1 Drain peak current 51 А Body-drain diode reverse drain current  $I_{DR}$ 17 А Body-drain diode reverse drain peak current 51 А I<sub>DR (pulse)</sub> I<sub>AP</sub><sup>Note3</sup> Avalanche current 6 A EAR Note3 2 Avalanche energy mJ Pch Note2 W Channel dissipation 100 Channel to case thermal impedance θch-c 1.25 °C/W 150 Channel temperature Tch °C °C Storage temperature Tstg -55 to +150

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc = 25°C

3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C





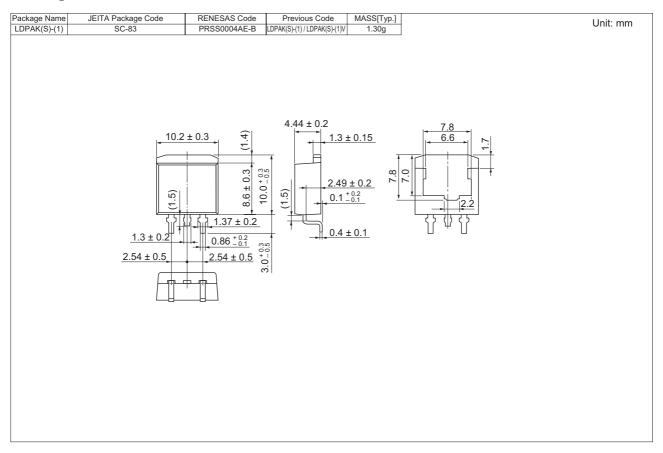
# **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	400	—	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS} = 400 V, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>		—	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{\text{DS(on)}}$		0.25	0.30	Ω	$I_D = 8.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	1450	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	175	_	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss		21	_	pF	
Turn-on delay time	t <sub>d(on)</sub>		33		ns	I <sub>D</sub> = 8.5 A
Rise time	tr	_	28	—	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	t <sub>d(off)</sub>	_	84	—	ns	$R_{L} = 23.5 \Omega$ $Rg = 10 \Omega$
Fall time	t <sub>f</sub>	_	15	—	ns	
Total gate charge	Qg		38	—	nC	V <sub>DD</sub> = 320 V
Gate to source charge	Qgs	_	8	—	nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 17 A
Gate to drain charge	Qgd	_	17	—	nC	
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.9	1.5	V	$I_F = 17 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>		260		ns	$I_F = 17 \text{ A}, V_{GS} = 0$ di <sub>F</sub> /dt = 100 A/µs

Notes: 4. Pulse test



# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK4013DPE-00-J3	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



# RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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## Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

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